



Fabrication and Characterization of Silicon
Based Vertical Electrode Nanogap Biosensor for
Protein Detection

By

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A thesis submitted

In fulfillment of the requirements for the degree of
Master of Science (Microelectronic Engineering)

School of Microelectronic Engineering

UNIVERSITI MALAYSIA PERLIS

2009

UNIVERSITI MALAYSIA PERLIS

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Academic Session : 2006 – 2009

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ACKNOWLEDGEMENT

I would like to acknowledge and express the greatest gratitude to my supervisor Prof. Dr. Uda Hashim, not only for giving me the opportunity to work in his group, but also for his encouragement, supervision, and guidance throughout this whole research work. His invaluable knowledge and suggestion had develop and grown up my experience and my skills in this nanotechnology. It has been great experience in the Nano Biochip Research Group.

Many colleagues have worked closely with me on this research. I would like to thank everyone in the Nano Biochip Research Group namely Muhammad Emi Azri, Ahmad Muzri, Cikgu Kassim, Chin Seng Fatt, and others. I do appreciate the constant help from lab technicians who always understand and their great help during the process of completing this research.

Last but not least, to my family especially my parents for their love, confidence, and support throughout my studies. Not forgetting my fellow friends of the post-graduate studies.

May Allah bless you all for those who are not mentioned.

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FABRIKASI DAN PENCIRIAN PENDERIA-BIO SELA-NANO ELEKTROD TEGAK BERDASAR SILIKON UNTUK PENGESANAN PROTEIN

ABSTRAK

Penderia-bio sela-nano merupakan peranti kelas baru yang telah menarik perhatian dan minat yg mendalam di kalangan penyelidik diatas potensi mereka di dalam aplikasi nanoteknologi. Peranti sela-nano ini yang difabrikasi menggunakan teknologi piawai Semikonduktor Komplimentari Logam Oksida (CMOS), mempunyai potensi untuk beroperasi sebagai simpang bio-molekul berikutan saiznya yang mengurangkan kesan pengutuban elektrod dengan menghiraukan frekuensi. Teknologi simpang ini adalah sistem penukar biologi-kepada-digital yang membolehkan penukaran masa nyata isyarat dielektrik bio-molekul kepada maklumat digit. Penderia-bio sela-nano ini mengandungi elektrod substratum silikon yang didop berat dan elektrod polisilikon yang dipisahkan secara tegak oleh peruang silikon oksida dengan jarak tetap 80nm. Pembangunan proses aliran di dalam penyelidikan ini mengandungi parameter – parameter dan resipi – resipi terperinci untuk menakrif peruang sela-nano ini. Dua (2) jenis topeng kerintangan digunakan di dalam proses ini iaitu Topeng Kerintangan Elektrod dan juga Topeng Kerintangan Pad Aluminium. Kedua – dua topeng kerintangan ini direkabentuk menggunakan perisian AutoCAD dan rekabentuknya dipindahkan ke atas topeng keringatan jenis lutsinar. Fokus utama penyelidikan ini ialah untuk menghasilkan peruang sela dengan menggunakan kaedah Plasma Terganding Beraruhan – Pemunar Ion Bertindak Balas (ICP – RIE) untuk memunar lapisan polisilikon dan asid hidroflorik (HF) penimbal untuk memunar lapisan silikon oksida. Walau bagaimanapun, silikon oksida tersebut tidak dipunar sepenuhnya, supaya lapisan yang tertinggal akan bertindak sebagai peruang sela mekanikal. Langkah terakhir melibatkan proses pemercitan dan pencorakkan aluminium ke atas pad sentuh menggunakan teknik piawai litografi-foto. Ini dilakukan untuk membantu mengurangkan kebolehubahan di dalam rintangan sentuhan apabila peranti sela-nano ini dikuarkan. Matlamat utama di dalam penyelidikan ini adalah untuk merekabentuk, memfabrikasi, mencari, dan menguji penderia-bio sela-nano elektrod tegak berdasar silikon yang akan digunakan untuk mengesan protein sasaran di dalam larutan berair.



FABRICATION AND CHARACTERIZATION OF SILICON BASED VERTICAL ELECTRODE NANOGAP BIOSENSOR FOR PROTEIN DETECTION

ABSTRACT

The nanogap biosensor is a new class of device that has attracted attention and great interest among the researchers due to their potential applications in nanotechnology. This nanogap device which are fabricated using standard Complimentary Metal Oxide Semiconductor (CMOS) technology, have the potential to serve as the biomolecular junctions because their size reduces electrode polarization effects regardless of frequency. This junction technology is essentially a biology-to-digital converter system that enables real time conversion of biomolecular dielectric signals into digital information. This nanogap biosensor consists of a heavily doped silicon substrate electrode and poly-silicon electrode vertically separated by a fixed distance of 80 nm silicon oxide spacer. The process flow development in this research consists of detailed parameters and recipes to define the nanogap spacer. Two (2) types of masks are used in the process which are the Electrode Mask and the Aluminum Pad Mask. Both masks are designed by using the AutoCAD software and transferred onto a transparency. The main focus in this research is to create the gap spacer by using Inductive Coupled Plasma – Reactive Ion Etch (ICP- RIE) to etch the poly-silicon layer and buffered hydrofluoric acid (HF) to etch the silicon oxide layer. However, the silicon oxide was not completely etched, so that the remaining will act as the mechanical spacer gap. The final step involved sputtering and patterning aluminum onto contact pads using a standard photolithography technique. This was done to help minimize the variability in contact resistance when the nanogap device was probed. The overall goal of this research is to design, fabricate, characterize, and test the silicon based vertical electrode nanogap biosensor that will be used to detect and identify target proteins in aqueous solution.

TABLE OF CONTENTS

	PAGES
APPROVAL OF DECLARATION SHEET	i
ACKNOWLEDGEMENT	ii
ABSTRAK	iii
ABSTRACT	iv
TABLE OF CONTENTS	v
LIST OF TABLES	viii
LIST OF FIGURES	ix
GLOSSARY OF ABBREVIATIONS	xv
LIST OF APPENDICES	xvii

CHAPTER 1

BACKGROUND

1.1	Introduction	1
1.2	Overview of Biosensor	3
1.3	Problem Statement	6
1.4	Objectives	8
1.5	Research Scope	9
1.6	Dissertation Layout	9

CHAPTER 2

LITERATURE REVIEW

2.1	Introduction	11
2.2	Nanobiotechnology	13
2.3	Nanosensor	15
	2.3.1 Nanogap Biosensor	18

2.3.2	Fabrication of Nanogap Biosensor	19
2.4	Dielectric Spectroscopy	23
2.5	Protein	25
2.5.1	Structure and Function of Proteins	28
2.5.2	Proteins' Electronic Properties	34
2.5.3	Electronic Detection of Proteins	37
2.6	Summary	39

CHAPTER 3 MASK DESIGN

3.1	Introduction	40
3.2	Mask Technology	41
3.3	Mask Design Methodology	44
3.3.1	Electrode Mask	45
3.3.2	Aluminum Pad Mask	50
3.4	Summary	54

CHAPTER 4 VERTICAL ELECTRODE NANOGAP FABRICATION AND CHARACTERIZATION

4.1	Introduction	55
4.2	Equipments and Consumable	56
4.2.1	Equipments	56
4.2.1	Consumables	57
4.3	Process Development	58
4.3.1	Substrate Material	59
4.3.2	Wafer Cleaning Process	60
4.3.3	Materials Deposition	63
4.3.4	Electrode Mask Patterning	69

4.3.5	Nanogap Formation	74
4.3.6	Aluminum Layer Sputtering Process	86
4.3.7	Aluminum Pad Mask Patterning	89
4.3.8	Aluminum Pad Formation	91
4.4	Nanogap Spacer Characterization	93
4.5	Summary	99

CHAPTER 5**CONCLUSION**

5.1	Introduction	100
5.2	Conclusion	100
5.3	Recommendation	101

REFERENCES

103

APPENDICES

LIST OF TABLES

TABLES	TITLE	PAGES
Table 4.1	List of equipment and its purposes	56
Table 4.2	Consumables and their purposes	57
Table 4.3	Process steps for vertical electrode nanogap fabrication	58
Table 4.4	The silicon wafer specifications	60
Table 4.5	Process recipe for silicon oxide layer deposition	65
Table 4.6	Process recipe for poly-silicon layer deposition	68
Table 4.7	ICP-RIE process recipe for poly-silicon etch	76
Table 4.8	Buffered HF silicon oxide layer wet etching condition	78

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LIST OF FIGURES

FIGURES	TITLE	PAGES
Figure 1.1	Example of a DNA Chip for Infectious Disease Diagnosis	1
Figure 1.2	Example of a protein chip	2
Figure 1.3	Schematic diagram of main components of biosensor (a) biocatalyst (b) transducer (c) amplifier (d) processor (e) display	4
Figure 1.4	A 96-well microtiter plate being used for ELISA	7
Figure 2.1	Block diagram of the early version of scanning probes, where (a) AFM and (b) STM	12
Figure 2.2	Selected aspects of interacting aspects of nano and biotechnology from materials to devices applications	14
Figure 2.3	A nanosensor probe carrying a laser beam (blue light) penetrates a living cell to detect the presence of a product indicating that the cell has been exposed to cancer-causing substance	16
Figure 2.4	Schematic representation of the nanogap biosensor structure where the two parallel electrodes are separated by a thin silicon oxide	18
Figure 2.5	An image of a fabricated nanogap structure with a 150nm oxide gap	20
Figure 2.6	SEM image of basic nanogap structure. Gap heights are determined by the thickness of silicon dioxide (20 – 300 nm)	21
Figure 2.7	SEM images of poly-silicon/gold (Au) nanogap electrodes. (a) Formation of Au/Ti electrode using sputter and lift-off. (b) SEM micrograph of 9.8 nm poly-	22

	silicon/Au nanogap	
Figure 2.8	(a) Schematic representation of the presented device, integrated into a crossbar array and (b) cross-sectional TEM image of the gap area where the gap is 2.5 nm high and 89 nm deep	23
Figure 2.9	Schematic showing (a) SEM image of a nanogap and (b) nanogap filled with electrolytes (two length scales, gap size L and electrical double layer thickness κ^{-1} , exist	24
Figure 2.10	The DNA sequence of a gene encodes the amino acid sequence of protein	26
Figure 2.11	Primary structure of protein	29
Figure 2.12	Protein secondary structure	30
Figure 2.13	The parallel and antiparallel of beta pleated sheet secondary protein structure	31
Figure 2.14	Proteins tertiary folding structure	32
Figure 2.15	Quaternary structure of protein	32
Figure 2.16	Image of sickle cell anemia and comparison with normal cells	33
Figure 2.17	Experimental set-up measuring nanogap capacitance.	37
Figure 3.1	Schematic showing on how the lithography works	41
Figure 3.2	The evolution of lithography wavelength corresponding to different light sources	42
Figure 3.3	Schematic showing blank substrate	43
Figure 3.4	A pellicle is attached to the mask over the array of row	43
Figure 3.5	Flow chart for the mask design methodology	45
Figure 3.6	Electrode Mask AutoCAD design	46
Figure 3.7	Schematic showing the parameters for the electrode mask design	48
Figure 3.8	Electrode design on a transparency mask	48
Figure 3.9	Single electrode design on transparency mask with	49

	measurements in 0.8X magnification	
Figure 3.10	Gold pad mask AutoCAD design	51
Figure 3.11	Parameters for gold contact pad. (a) Contact on the top electrode and (b) Contact for the bottom electrode	51
Figure 3.12	Gold pad design on a transparency mask	52
Figure 3.13	The contact pad for the top electrode design on a transparency mask with measurements in 0.8X magnification	53
Figure 3.14	The contact pad for the bottom electrode design on a transparency mask with measurements in 1.0X magnification	53
Figure 4.1	Process steps for vertical electrode nanogap fabrication	60
Figure 4.2	N-type silicon wafer	59
Figure 4.3	Wet Cleaning Bench	61
Figure 4.4	Images under HPM of (a) Wafer 1 and (b) Wafer 2, before cleaning process	62
Figure 4.5	Images under HPM of (a) Wafer 1 and (b) Wafer 2, after RCA and BOE cleaning procedure	62
Figure 4.6	The Plasmalab 80Plus PECVD	64
Figure 4.7	Schematic showing the nine (9) reading points on the wafer surface	65
Figure 4.8	Filmetrics F20 Spectrophotometer to measure film thickness	66
Figure 4.9	Graph of silicon oxide thickness for two wafer samples	67
Figure 4.10	Graph showing the different thickness of poly-silicon layer for 2 wafer samples	68
Figure 4.11	Schematic drawing of positive photoresist coated on the poly-silicon layer	70
Figure 4.12	Single wafer spinner for photoresist spin coating	71
Figure 4.13	MIDAS MDA 400M mask aligner and exposure system	72

Figure 4.14	Schematic drawing of (a) The electrode mask is being exposed onto the photoresist for pattern transfer. (b) The remaining resist after developing process of creating the pattern of the mask design	72
Figure 4.15	The optical microscope top view image after photoresist developing process with 100X magnification, where (a) the area between contact pad and electrode and (b) the electrode area	73
Figure 4.16	SAMCO Inductive coupled plasma-Reactive ion etch (ICP-RIE) system	75
Figure 4.17	Schematic drawing of (a) poly-silicon layer before etching and (b) anisotropic tapered profile of poly-silicon layer	75
Figure 4.18	SEM images of structure after poly-silicon RIE under various time where (a) 30 seconds (b) 35 seconds, and (c) 40 seconds. Image (a) shows each layer of the structure.	77
Figure 4.19	Schematic drawing of (a) silicon oxide layer before etching process and (b) poly-silicon under-etch producing a silicon oxide spacer or gap	79
Figure 4.20	Schematic drawing of (a) positive photoresist before stripping process and (b) final structure after photoresist stripped	80
Figure 4.21	Nanogap spacer image obtained using SEM. This image represents the gap of silicon oxide thickness of 80 nm	81
Figure 4.22	SEM images of gap spacer with silicon oxide thickness of 80nm of (a) 35 min, (b) 40 min, and (c) 45 min	82
Figure 4.23	Graph of etch time versus under-etch distance for 80 nm gap spacer	83
Figure 4.24	N-type diffusion furnace to diffuse phosphorus	84

Figure 4.25	Loading wafers into the n-type diffusion furnace using the quartz rod	84
Figure 4.26	The four point probe station to measure sheet resistance	85
Figure 4.27	Sheet resistance measurements of the structure before and after the doping process of phosphorus	86
Figure 4.28	Schematic drawing of a 200nm gold layer sputtered onto the vertically separated nanogap structure	87
Figure 4.29	The Aluminum Evaporator (PVD) Sputtering System	87
Figure 4.30	Images showing results after aluminum sputtering process using a high power microscope with 100X magnification	88
Figure 4.31	Schematic of the cross-section of (a) Contact mask being exposed onto the photoresist for pattern transfer. (b) The remaining photoresist after developing process creating the pattern of the mask design	90
Figure 4.32	Images of structure after developing process where (a) under-develop and (b) fully develop	91
Figure 4.33	Schematic structure of the device in cross-section (a) after the Al layer has been etched out and (b) the photoresist has been stripped using acetone and Al will act as a contact pad	92
Figure 4.34	The resist layer after etching process at various etching times (a) 5 min, (b) 10 min and (c) 15 min	93
Figure 4.35	The SPA system used for characterization process	94
Figure 4.36	Schematic showing the nanogap device is being probed onto the top and bottom electrode Al contact pad	94
Figure 4.37	The probe station of the SPA to test the C-V characteristic of the device	95
Figure 4.38	C-V characteristic for low frequency input of 10 kHz	98

Figure 4.39	C-V characteristic for high frequency input of 1 MHz	97
Figure 4.40	Graph of I-V characteristic for the 80 nm gap spacer	98

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GLOSSARY OF ABBREVIATIONS

AFM	=	Atomic Force Microscope
AR	=	Anti Reflective
BAPP	=	Beta-Amyloid Precursor Protein
BOE	=	Buffered Oxide Etch
BSE	=	Bovine Spongiform Encephalopathy
CD	=	Critical Dimension
CJD	=	Creutzfeldt-Jakob Disease
CMOS	=	Complementary Metal Oxide Semiconductor
DI	=	Dionized
DNA	=	Deoxyribonucleic Acid
DS	=	Dielectric Spectroscopy
EBL	=	Electron Beam Lithography
EDL	=	Electric Double Layer
ELISA	=	Enzyme-Linked Immunosorbent Assay
EUV	=	Extreme Ultraviolet Lithography
HCL	=	Hydrochloric Acid
HF	=	Hydrofluoric Acid
HPM	=	High Power Microscope
HNO ₃	=	Nitric Acid
ICP-RIE	=	Inductive Coupled Plasma-Reactive Ion Etching
KOH	=	Potassium Hydroxide
LPCVD	=	Low Pressure Chemical Vapor Deposition
NH ₄ F	=	Ammonium Fluoride
PECVD	=	Plasma Enhanced Chemical Vapor Deposition
PVD	=	Physical Vapor Deposition (Aluminum Evaporator)
QM	=	Quantum Mechanics
RIE	=	Reactive Ion Etching
RNA	=	Ribonucleic Acid

SC	=	Standard Cleaning
SEM	=	Scanning Electron Microscope
SOI	=	Silicon on Insulator
SPA	=	Semiconductor Parameter Analyzer
STM	=	Scanning Tunneling Microscope
TMAH	=	Tetramethyl Ammonium Hydroxide

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LIST OF APPENDICES

APPENDIX	TITLE
A	Process Flow
B	Process Runcard
C	Publications & Awards

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CHAPTER 1

BACKGROUND

1.1 Introduction

Understanding the relationship between protein structure and its function is paramount to unlocking life's processes on a molecular scale, and it is important to develop efficient measurement tools necessary to record these relationships. Previously, researchers have extensively developed Deoxyribonucleic acid (DNA) chips for gene expression profiling and mutation mapping (Thomas, Hopkins, & Brady, 1998; Chang et al., 2007) over the past decade as seen in Figure 1.1. Wang et al. (2001) have reported electrochemical detection of DNA using magnetic particles for separation and concentration of target DNA.

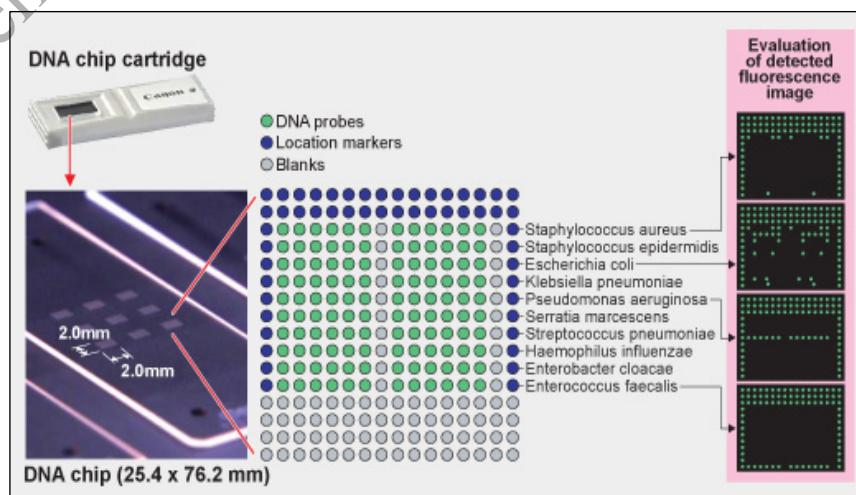


Figure 1.1: Example of a DNA Chip for Infectious Disease Diagnosis (“DNA Chip Fabrication Technology”, 2008)

Since the activity of encoded proteins can directly manifest gene function (Emili, & Cagney, 2000) and plays an essential role in molecular biological analysis (Kelvin, 2001), researchers and scientists must develop a protein biochip or biosensor that can identify target proteins and provide information that is useful to many medical applications including the diagnosis of cancer in the early stage and drug discovery.

The basic construction concept of a protein chip, as seen in Figure 1.2, is somewhat similar to the DNA chip because it has a glass, plastic, and a silicon oxide surface immobilized with bio-molecules (Chang et al., 2007). Bio-molecules functional magnetic particles have been extensively applied in various bioelectronic applications.

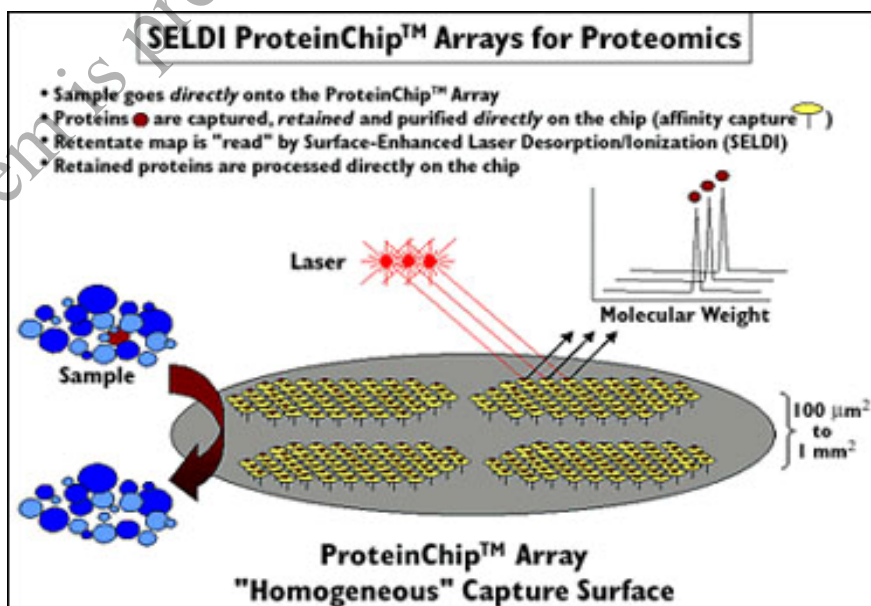


Figure 1.2: Example of a protein chip (DeFrancesco, 1999)

These bio-molecules are the fundamental building blocks of living cells such as double stranded DNA, protein structure and antibodies. The bio-molecules have been electrically characterized predominantly by a single or few molecule experiments (Joachim, 2000; Mayor, 2003; Rutkowski et al., 2005). Specific junctions between the cells of these bio-molecules conduct electrical and chemical signals that result from various kinds of stimulation. The output signals will provide information of normal functions of the cells such as energy storage, information storage and retrieval, tissue regeneration, and sensing (Frank, n.d).

In this chapter, an overview of biosensors and biomolecules will be presented, and the discussion continues with the objectives of this research, the research scope, the problem statement and lastly the whole dissertation layout of this thesis.

1.2 Overview of Biosensor

A biosensor is an analytical device which converts a biological response into an electrical signal as seen in Figure 1.3. The term biosensor is often used to cover sensor devices used in order to determine the concentration of substances and other parameters of biological interest even when they do not utilize a biological system directly (Chaplin, 2004).

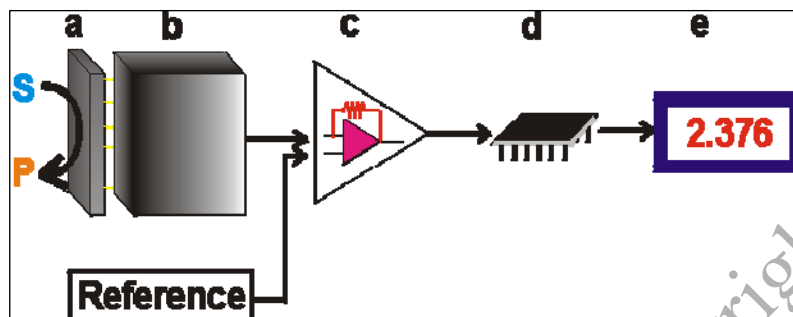


Figure 1.3: Schematic diagram of main components of biosensor (a) biocatalyst (b) transducer (c) amplifier (d) processor (e) display (Chaplin, 2004)

Many of today's biosensor applications are similar, in that they use organisms which respond to toxic substances at a much lower level than human to warn us of their presence. Such devices can also be used in both environmental monitoring and water treatment facilities (Chaplin, 2004).

Biosensors have the potential to affect many areas. Field application areas including medicine, physical therapy, music, and the video game industry, can all benefit from the introduction of biosensors (Tonnesen, & Withrow, 2008). The most widespread example of a commercial biosensor is the blood glucose biosensor, which uses an enzyme to break blood glucose down.

Biosensors are typically classified by the type of recognition element or transduction element employed. A sensor might be described as a catalytic biosensor if its recognition element comprised an enzyme or series of enzymes, a living tissue slice (vegetal or animal), or whole cells derived from microorganisms such as bacteria, fungi, or yeast. The sensor might be described as a bio-affinity

sensor if the basis of its operation were a bio-specific complex formation. Accordingly, the reaction of an antibody with an antigen or hapten, or the reaction of an agonist or antagonist with a receptor, could be employed. In the former case, the sensor might be called an immunosensor (Tonnesen, & Withrow, 2008).

There are three basic principles of detection of biosensors. Optical biosensors which are based on the phenomenon of surface plasmon resonance are evanescent wave techniques. This utilizes a property shown of gold and other materials, specifically that a thin layer of gold on a high refractive index glass surface can absorb laser light, producing electron waves on the gold surface ("Biosensors – Application and How Multiwalled Carbon Nanotubes Are Used In Sensor Production", 2008).

Electrochemical biosensors are normally based on enzymatic catalysis of a reaction that produces or consumes electrons where such enzymes are rightly called redox enzymes. The sensor substrate usually contains three electrodes, a reference electrode, an active electrode and a sink electrode. The target analyte is involved in the reaction that takes place on the active electrode surface, and the ions produced will create a potential which is subtracted from that of the reference electrode to give a signal (Yvon, 2008).

Piezoelectric sensors utilize crystals which undergo an elastic deformation when an electrical potential is applied to them. An alternating potential produces a standing wave in the crystal at a characteristic frequency. This frequency is highly dependent on the elastic properties of the crystal, such that if a crystal is coated with a biological recognition element the binding of a large target analyte to a receptor will produce a change in the resonance frequency, which gives a binding signal (Chaplin, 2004).

The quality of the results obtained from sensors based on biological recognition elements depends most heavily on their ability to react rapidly, selectively, and with high affinity. Antibodies and receptors frequently react with such high affinity that the analyte does not easily become unbound. To reuse the sensor requires a time-consuming regeneration step. Nonetheless, if this step can be automated, semi continuous monitoring may be possible (Yvon, 2008).

1.3 Problem Statement

Over the past years, several groups have reported on carbon nanotube, semiconductor nanowire chemical (Kong et al., 2008; Steuermann et al., 2002), and biomolecular sensors (Kong et al., 2008; Steuermann et al., 2002; Cui, Wei, Park, & Lieber, 2001). The biosensing applications are in many ways, driven by the emerging concepts of system biology (Davidson et al., 2003; Kitano, 2002) and the translation of those concepts into the clinic (Hood, Heath, Phelps, & Lin, 2004)